

25V NPN LOW SATURATION TRANSISTOR IN SOT23

Features

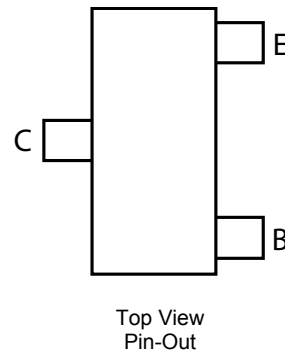
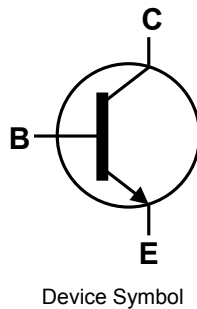
- $BV_{CEO} > 25V$
- $BV_{CBO} > 35V$ forward blocking voltage
- $I_C = 3A$ high Continuous Collector Current
- Low saturation voltage, $V_{CE(SAT)} < 120mV @ 1A$
- $R_{CE(SAT)} = 77m\Omega$ for a low equivalent On-Resistance
- 725mW Power dissipation
- h_{FE} specified up to 6A for high current gain hold up
- Complementary PNP Type: ZXTP749F
- **Totally Lead-Free & Fully RoHS compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**

Mechanical Data

- Case: SOT23
- Case Material: molded plastic, "Green" molding compound
- UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish – Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208 (E3)
- Weight 0.008 grams (approximate)

Applications

- MOSFET gate drivers
- Power switching in automotive and industrial applications
- Motor drive and control

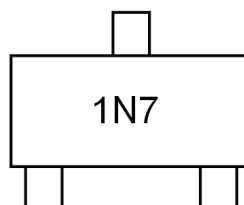


Ordering Information (Note 4)

Product	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
ZXTN649FTA	1N7	7	8	3,000

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
 2. See <http://www.diodes.com> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. For packaging details, go to our website at <http://www.diodes.com>.

Marking Information



1N7 = Product type Marking Code

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CB0}	35	V
Collector-Emitter Voltage	V _{CEO}	25	V
Emitter-Base Voltage	V _{EBO}	7	V
Continuous Collector Current	I _C	3	A
Peak Pulse Current	I _{CM}	6	A
Base Current	I _B	500	mA

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

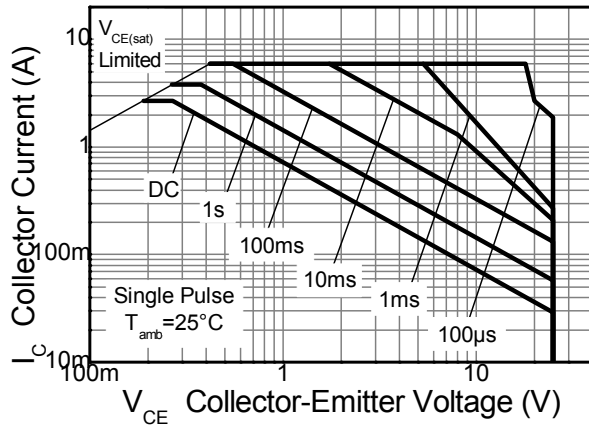
Characteristic	Symbol	Value	Unit
Power Dissipation (Note 5)	P _D	725	mW
Thermal Resistance, Junction to Ambient (Note 5)	R _{θJA}	172	°C/W
Thermal Resistance, Junction to Leads (Note 6)	R _{θJL}	79	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

ESD Ratings (Note 7)

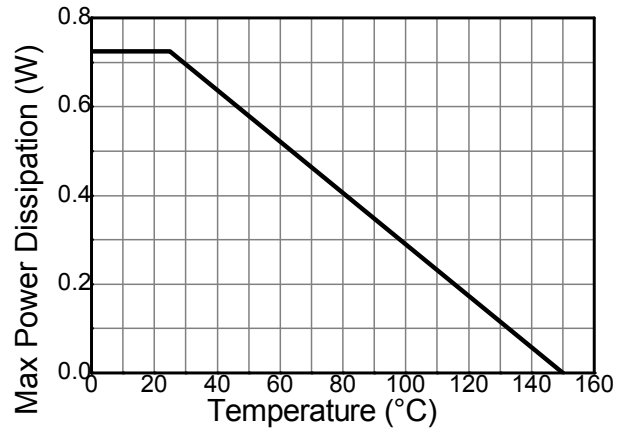
Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	≥ 8,000	V	3B
Electrostatic Discharge - Machine Model	ESD MM	≥ 400	V	C

- Notes:
5. For a device surface mounted on 15mm x 15mm x 1.6mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions; the device is measured when operating in a steady-state condition.
 6. Thermal resistance from junction to solder-point (at the end of collector lead).
 7. Refer to JEDEC specification JESD22-A114 and JESD22-A115.

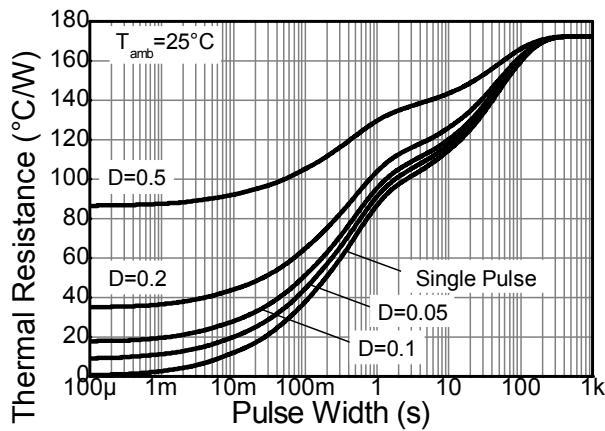
Thermal Characteristics and Derating information



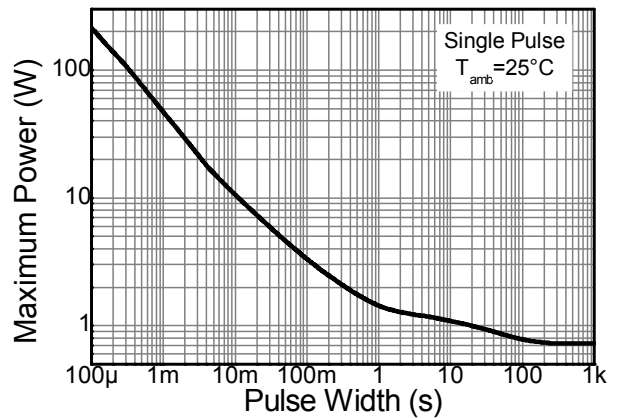
Safe Operating Area



Derating Curve



Transient Thermal Impedance



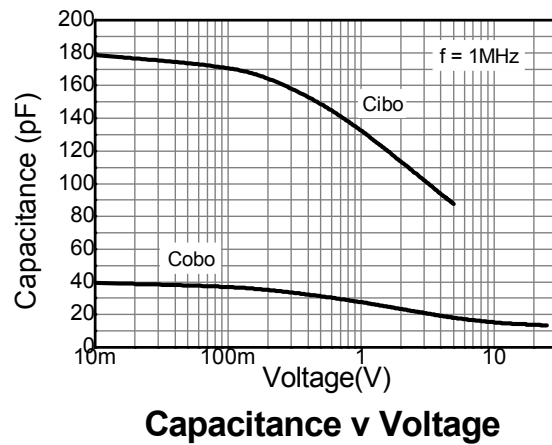
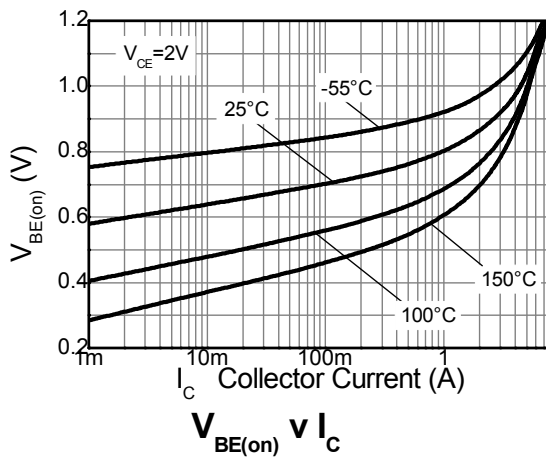
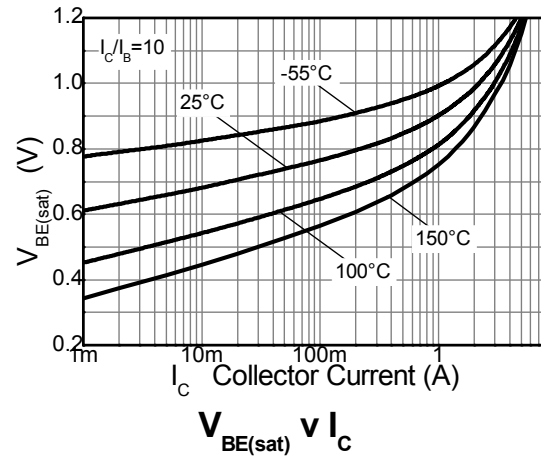
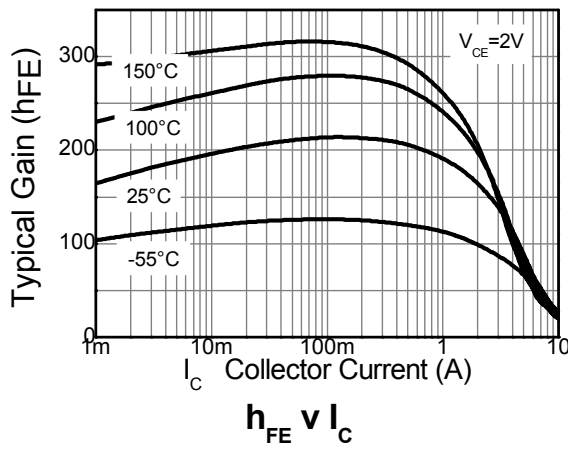
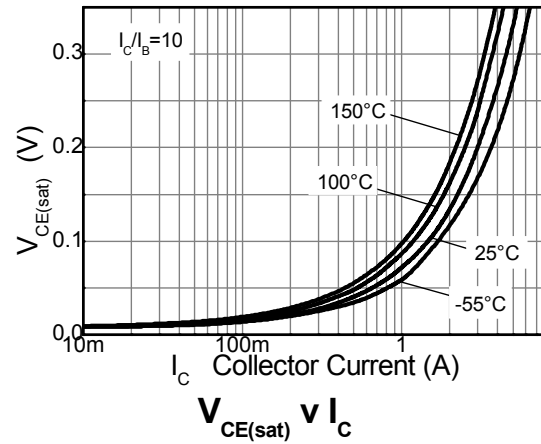
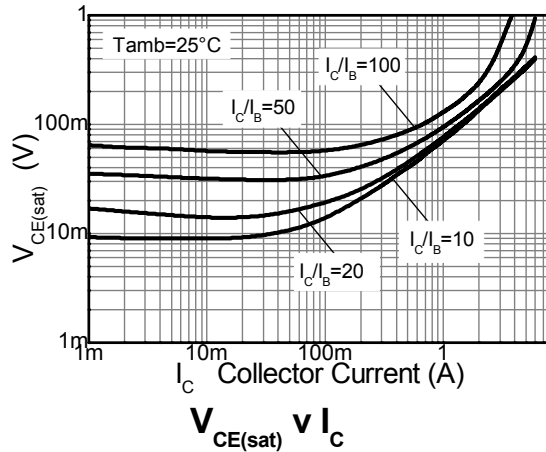
Pulse Power Dissipation

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV _{CBO}	35	110	-	V	I _C = 100μA
Collector-Emitter Breakdown Voltage (Note 8)	BV _{CEO}	25	35	-	V	I _C = 10mA
Emitter-Base Breakdown Voltage	BV _{EBO}	7	8.1	-	V	I _E = 100μA
Collector Cut-off Current	I _{CBO}	-	<1	50 0.5	nA μA	V _{CB} = 28V V _{CB} = 28V, T _A = +100°C
Emitter Cut-off Current	I _{EBO}	-	<1	50	nA	V _{EB} = 5.6V
Static Forward Current Transfer Ratio (Note 8)	h _{FE}	200 175 155 50	320 280 250 85	500 - - -	-	I _C = 100mA, V _{CE} = 2V I _C = 1A, V _{CE} = 2V I _C = 2A, V _{CE} = 2V I _C = 6A, V _{CE} = 2V
Collector-Emitter Saturation Voltage (Note 8)	V _{CE(sat)}	-	70 200	120 300	mV	I _C = 1A, I _B = 100mA I _C = 3A, I _B = 300mA
Base-Emitter Saturation Voltage (Note 8)	V _{BE(sat)}	-	900	1000	mV	I _C = 1A, I _B = 100mA
Base-Emitter Saturation Voltage (Note 8)	V _{BE(on)}	-	780	850	mV	I _C = 1A, V _{CE} = 2V

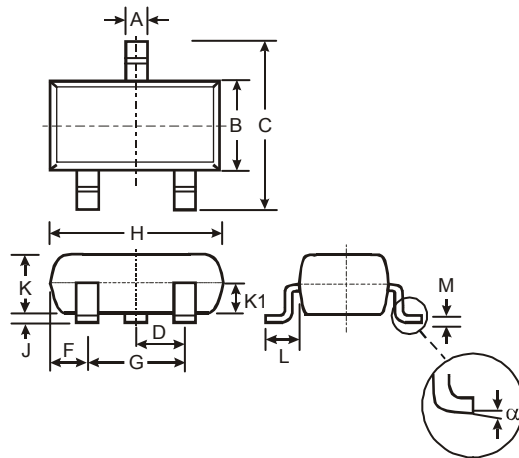
Notes: 8. Measured under pulsed conditions. Pulse width ≤ 300μs. Duty cycle ≤ 2%

Typical Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)



Package Outline Dimensions

Please see AP02002 at <http://www.diodes.com/datasheets/ap02002.pdf> for latest version.

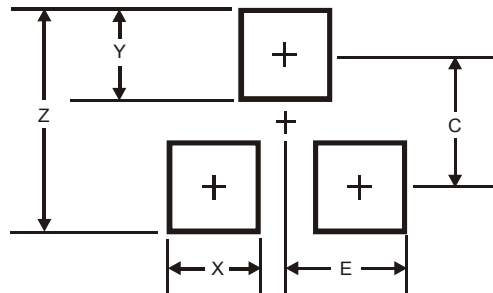


SOT23			
Dim	Min	Max	Typ
A	0.37	0.51	0.40
B	1.20	1.40	1.30
C	2.30	2.50	2.40
D	0.89	1.03	0.915
F	0.45	0.60	0.535
G	1.78	2.05	1.83
H	2.80	3.00	2.90
J	0.013	0.10	0.05
K	0.903	1.10	1.00
K1	-	-	0.400
L	0.45	0.61	0.55
M	0.085	0.18	0.11
α	0°	8°	-

All Dimensions in mm

Suggested Pad Layout

Please see AP02001 at <http://www.diodes.com/datasheets/ap02001.pdf> for the latest version.



Dimensions	Value (in mm)
Z	2.9
X	0.8
Y	0.9
C	2.0
E	1.35

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